

In the Specification:

Please amend Paragraph [0056] on page 17 as follows:

-- The hard mask 420 is removed, as shown in Figure 13. The recess above the deep trench in the first region 407 is left exposed, along with the shallow trench isolation region pattern 430 and the second region 410 412 of the semiconductor device 400. The pad nitride 406 is pulled back: the top edge surfaces are angled slightly as shown, for example, by approximately 100 to 200 Angstroms to obtain a better fill in the subsequent insulating layer deposition.--